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Si4505DY
Vishay Siliconix

N- and P-Channel MOSFET

PRODUCT SUMMARY

	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
N-Channel	30	0.018 at V _{GS} = 10 V	7.8
		0.027 at V _{GS} = 4.5 V	6.4
P-Channel	- 8	0.042 at V _{GS} = - 4.5 V	- 5.0
		0.060 at V _{GS} = - 2.5 V	- 4.0

FEATURES

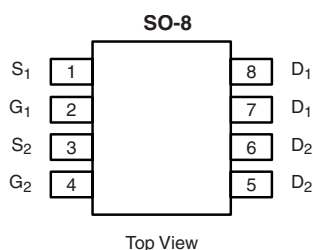
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Compliant to RoHS Directive 2002/95/EC



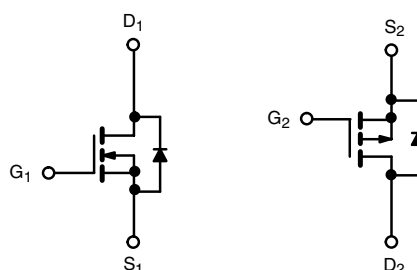
RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Level Shift
- Load Switch



Ordering Information: Si4505DY-T1-E3 (Lead (Pb)-free)
Si4505DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter		Symbol	N-Channel		P-Channel		Unit
			10 s	Steady State	10 s	Steady State	
Drain-Source Voltage		V _{DS}	30		- 8		V
Gate-Source Voltage		V _{GS}	± 20		± 8		
Continuous Drain Current (T _J = 150 °C) ^{a, b}	T _A = 25 °C	I _D	7.8	6.0	- 5.0	- 3.8	A
	T _A = 70 °C		6.0	5.2	- 3.6	- 3.0	
Pulsed Drain Current		I _{DM}	30		- 30		
Continuous Source Current (Diode Conduction) ^{a, b}		I _S	1.8	1.0	- 1.8	- 1.0	
Maximum Power Dissipation ^{a, b}	T _A = 25 °C	P _D	2	1.20	2	1.2	W
	T _A = 70 °C		1.3	0.75	1.3	0.75	
Operating Junction and Storage Temperature Range		T _J , T _{sta}	- 55 to 150				°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	N-Channel		P-Channel		Unit
		Typ.	Max.	Typ.	Max.	
Maximum Junction-to-Ambient ^a	R _{thJA}	50	62.5	50	62.5	°C/W
		85	105	85	105	
Maximum Junction-to-Foot (Drain)	R _{thJF}	30	40	30	40	

Notes:

a. Surface Mounted on FR4 board.

b. t ≤ 10 s.

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SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions		Min.	Typ. ^a	Max.	Unit	
Static								
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	N-Ch	0.8		1.8	V	
		V _{DS} = V _{GS} , I _D = - 250 μA	P-Ch	- 0.45		- 1.0		
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	N-Ch			± 100	nA	
		V _{DS} = 0 V, V _{GS} = ± 8 V	P-Ch			± 100		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	N-Ch			1	μA	
		V _{DS} = - 8 V, V _{GS} = 0 V	P-Ch			- 1		
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C	N-Ch			5		
		V _{DS} = - 8 V, V _{GS} = 0 V, T _J = 55 °C	P-Ch			- 5		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	N-Ch	20			A	
		V _{DS} = - 5 V, V _{GS} = - 4.5 V	P-Ch	- 20				
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 7.8 A	N-Ch		0.015	0.018	Ω	
		V _{GS} = - 4.5 V, I _D = - 5.0 A	P-Ch		0.030	0.042		
		V _{GS} = 4.5 V, I _D = 6.4 A	N-Ch		0.022	0.027		
		V _{GS} = - 2.5 V, I _D = - 4.0 A	P-Ch		0.048	0.060		
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 7.8 A	N-Ch		18		S	
		V _{DS} = - 15 V, I _D = - 5.0 A	P-Ch		12			
Diode Forward Voltage ^b	V _{SD}	I _S = 1.8 A, V _{GS} = 0 V	N-Ch		0.73	1.1	V	
		I _S = - 1.8 A, V _{GS} = 0 V	P-Ch		- 0.75	- 1.1		
Dynamic ^a								
Total Gate Charge	Q _g	N-Channel V _{DS} = 15 V, V _{GS} = 5 V, I _D = 7.8 A	N-Ch		11.5	20	nC	
Gate-Source Charge	Q _{gs}		P-Ch		13.5	20		
Gate-Drain Charge	Q _{gd}	P-Channel V _{DS} = - 4 V, V _{GS} = - 5 V, I _D = - 5.0 A	N-Ch		3			
			P-Ch		2.2			
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 15 V, R _L = 15 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _G = 6 Ω	N-Ch		15	25	ns	
			P-Ch		21	40		
	Rise Time		t _r	N-Ch		8		15
				P-Ch		45		70
Turn-Off Delay Time	t _{d(off)}	P-Channel V _{DD} = - 4 V, R _L = 4 Ω I _D ≅ - 1 A, V _{GEN} = - 4.5 V, R _g = 6 Ω	N-Ch		35	55		
			P-Ch		60	100		
Fall Time	t _f		N-Ch		10	20		
			P-Ch		55	85		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.8 A, dI/dt = 100 A/μs	N-Ch		30	60		
			P-Ch		50	100		

Notes:

a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

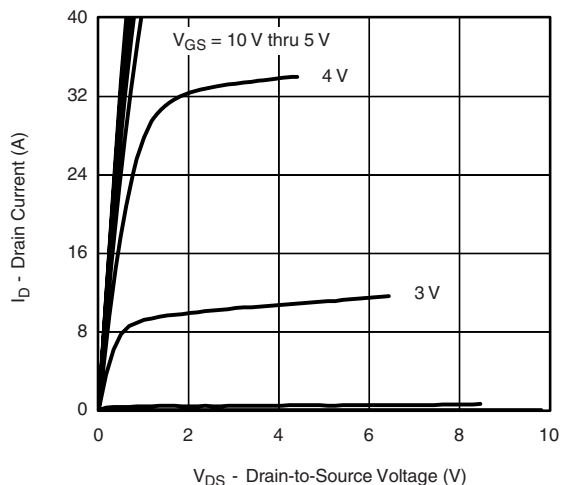
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



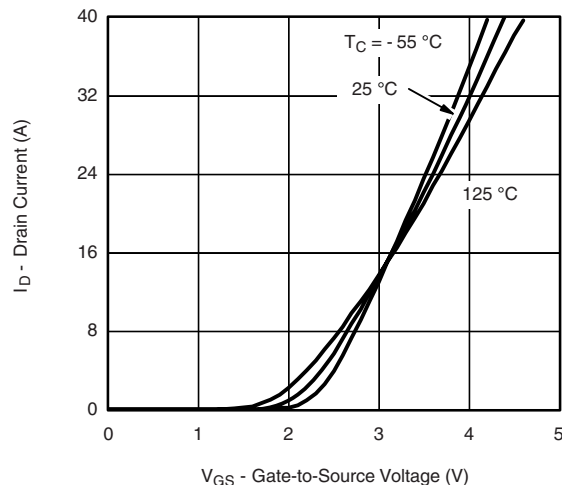
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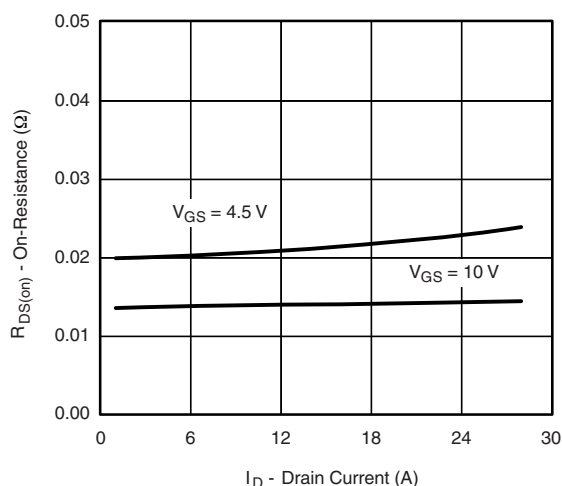
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



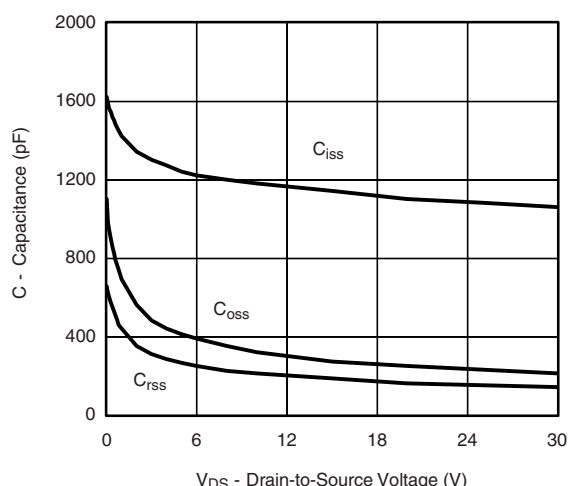
Output Characteristics



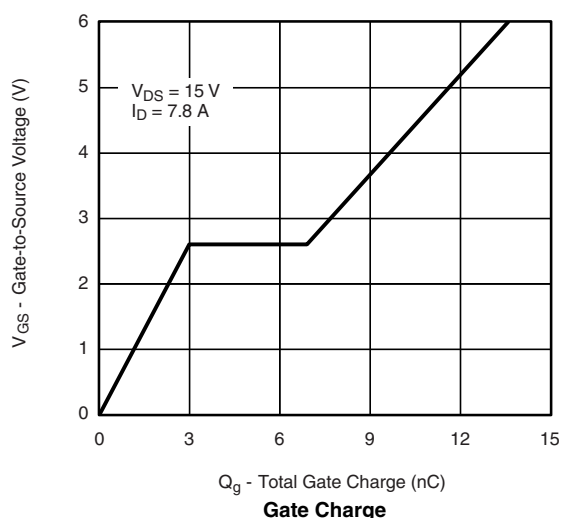
Transfer Characteristics



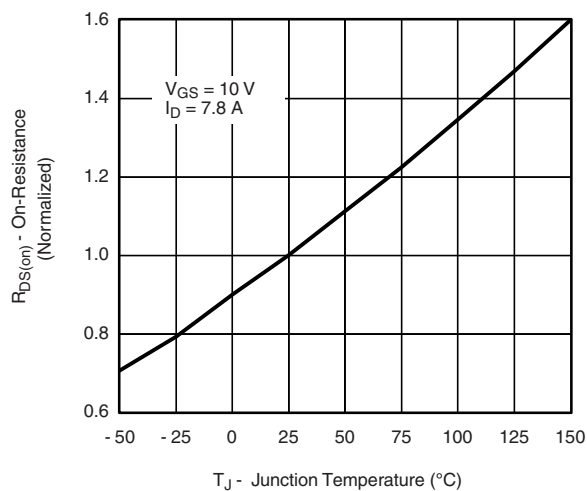
On-Resistance vs. Drain Current



Capacitance



Gate Charge



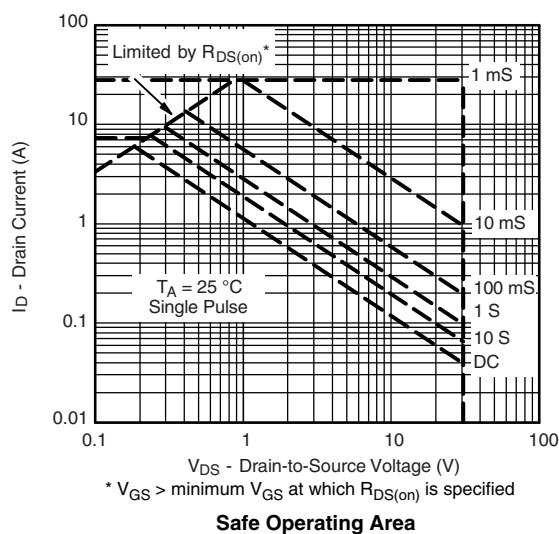
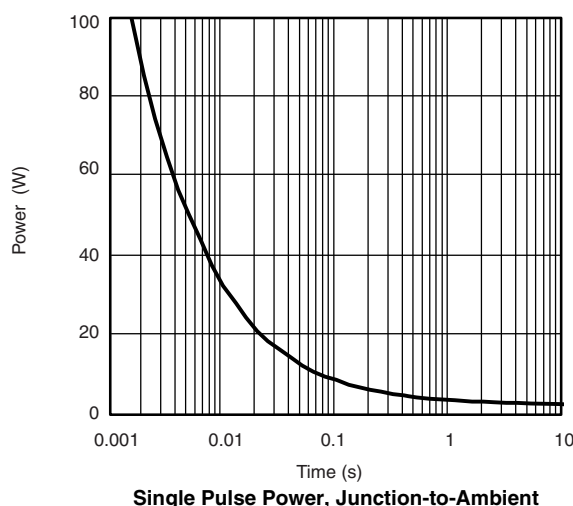
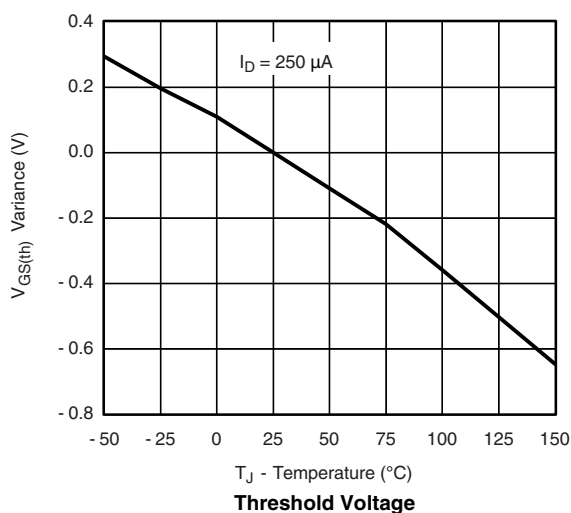
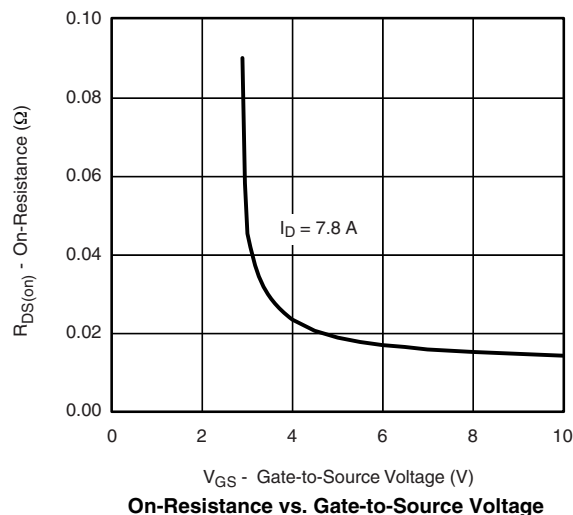
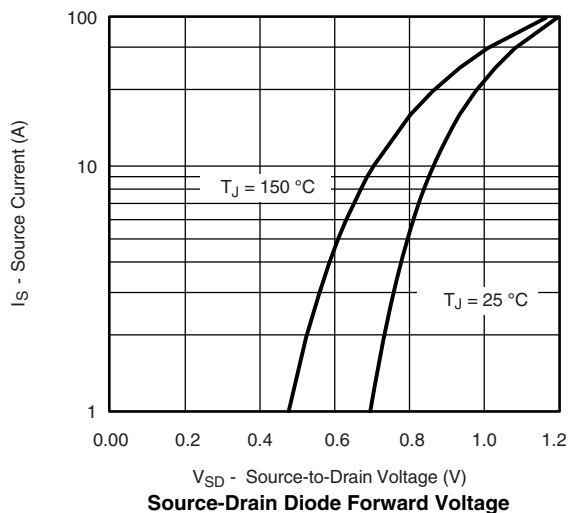
On-Resistance vs. Junction Temperature

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N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

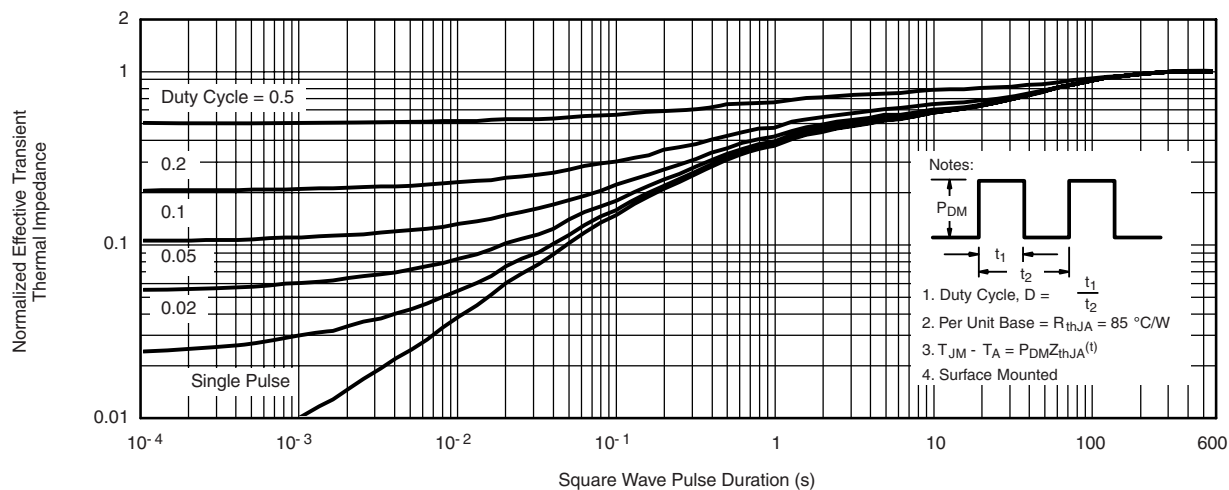




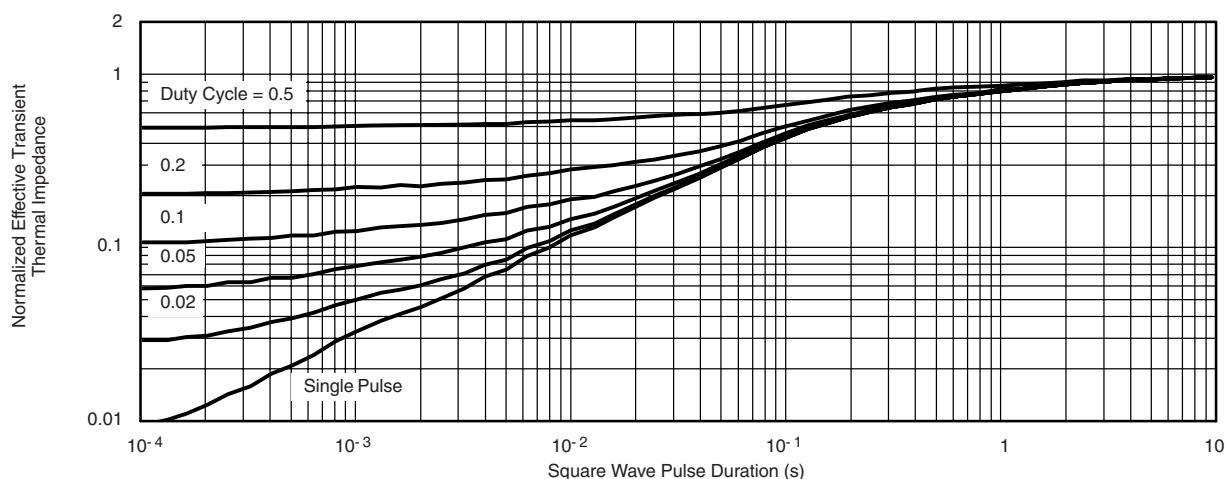
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N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



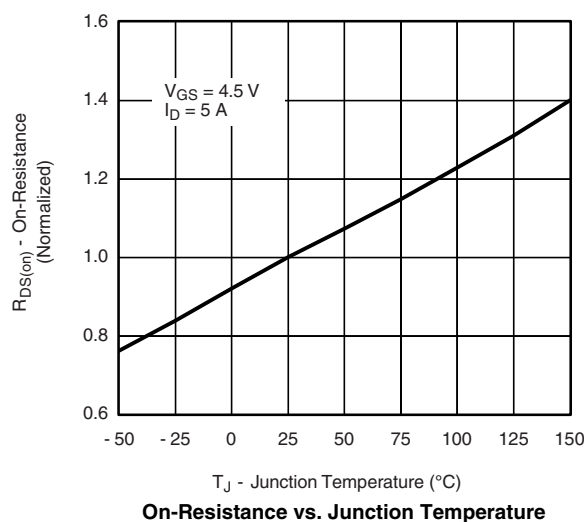
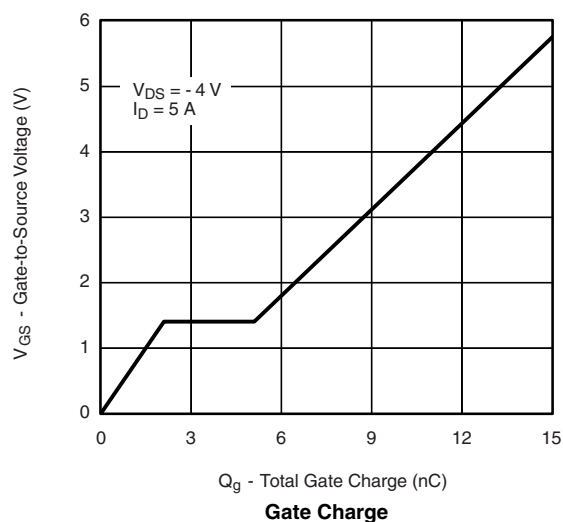
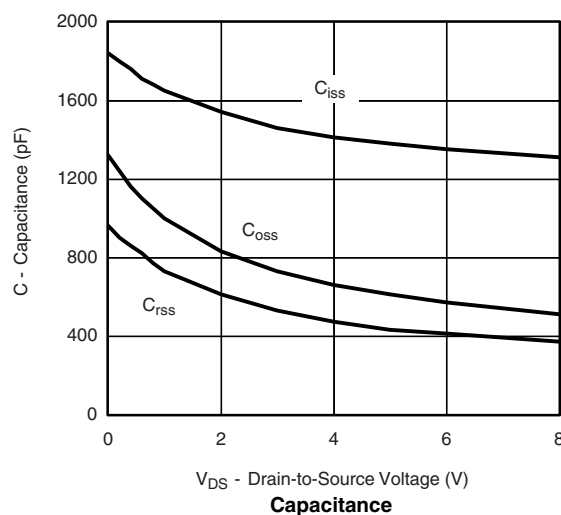
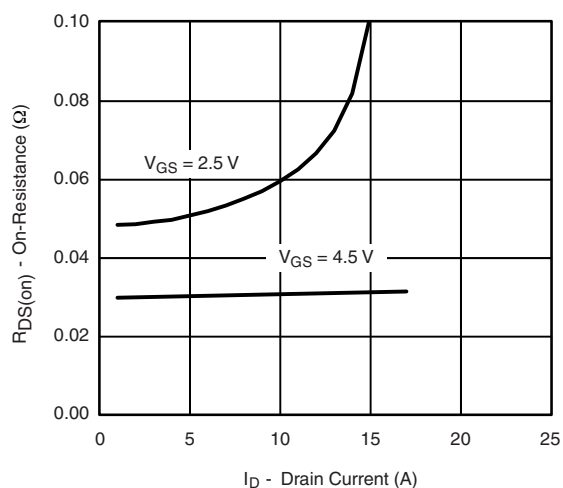
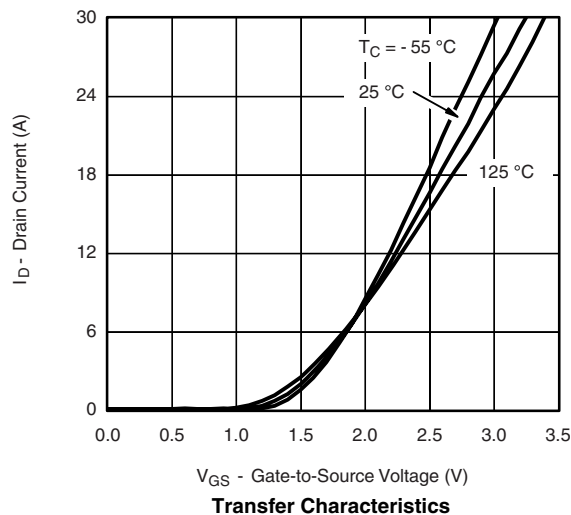
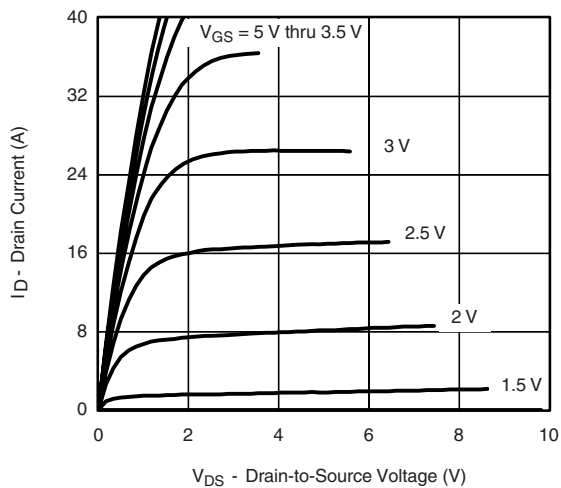
Normalized Thermal Transient Impedance, Junction-to-Foot

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P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

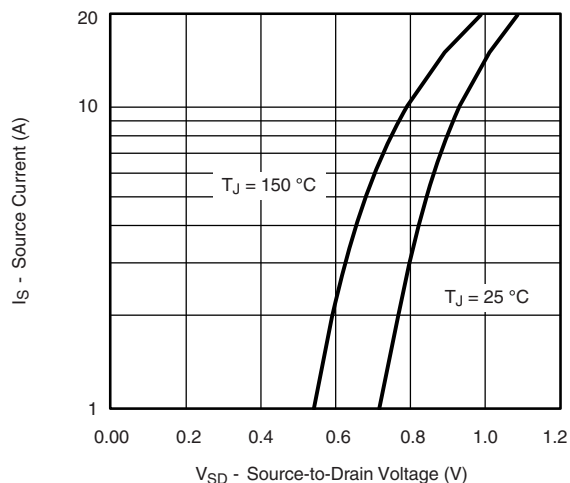




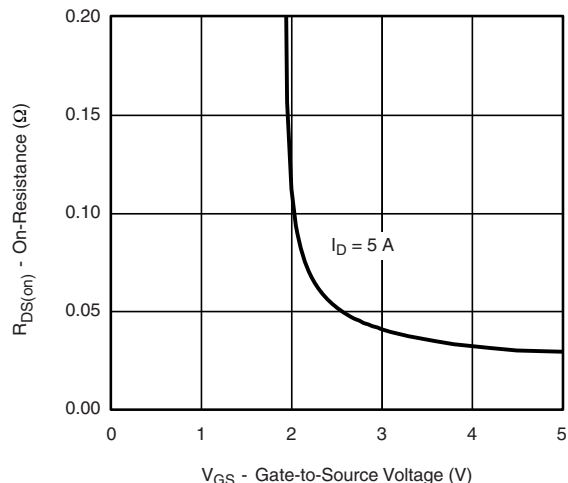
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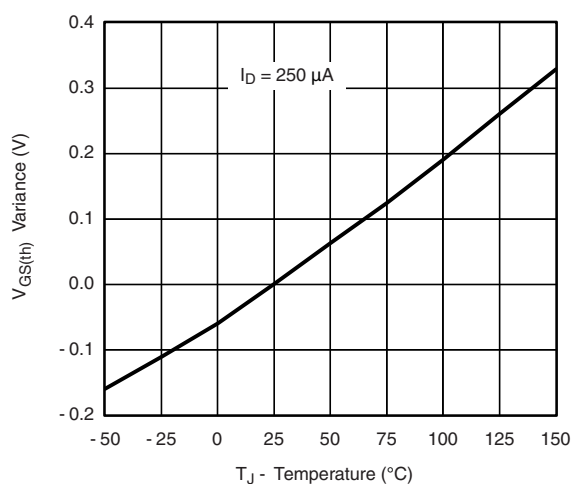
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



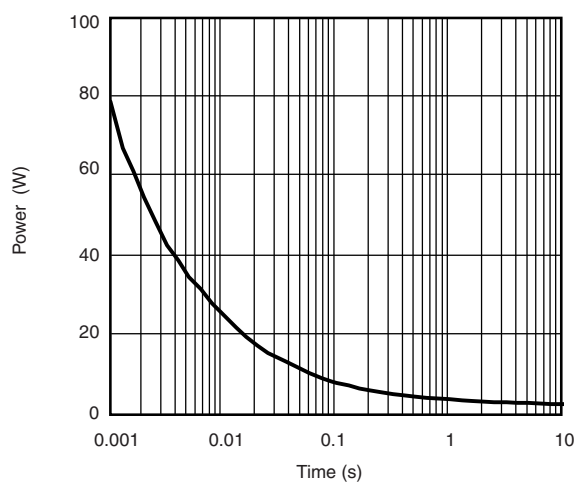
Source-Drain Diode Forward Voltage



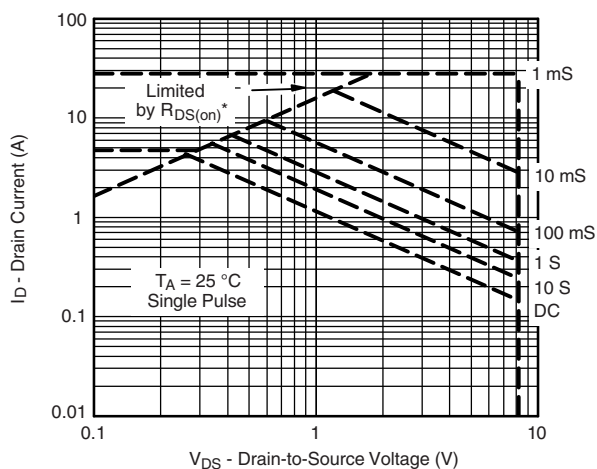
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

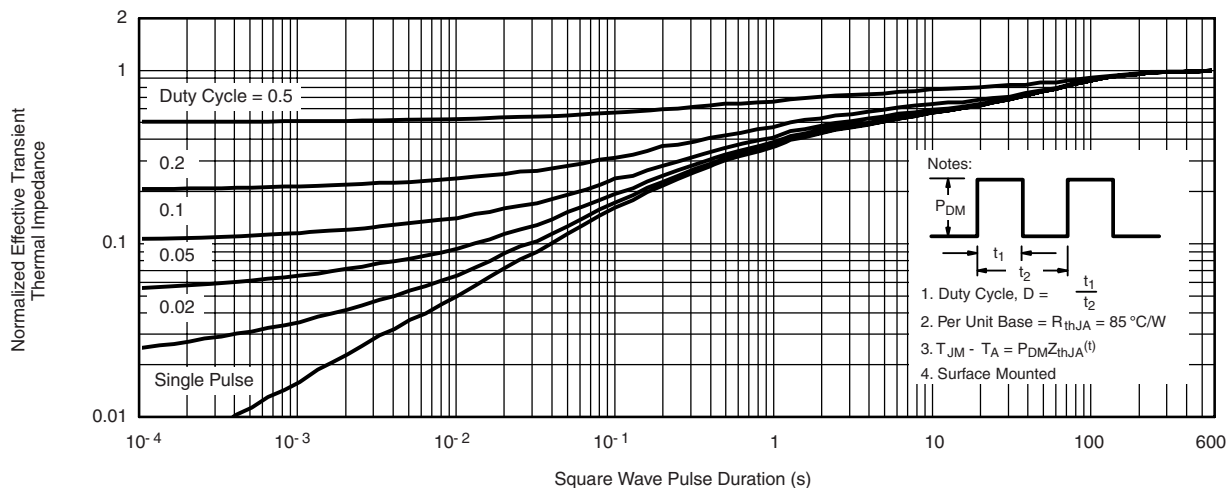
Safe Operating Area

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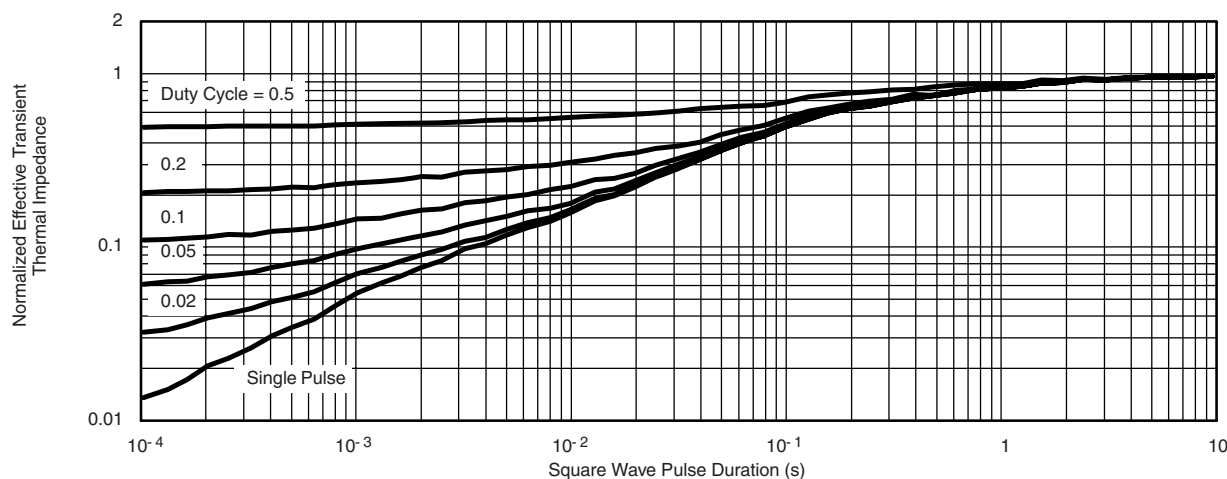
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P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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